

ESSDERC 2019 – 49th European Solid-State Device Research Conference (ESSDERC 2019)

**Cracow, Poland
23 – 26 September 2019**



**IEEE Catalog Number: CFP19543-POD
ISBN: 978-1-7281-1540-5**

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IEEE Catalog Number:	CFP19543-POD
ISBN (Print-On-Demand):	978-1-7281-1540-5
ISBN (Online):	978-1-7281-1539-9
ISSN:	1930-8876

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